

substrate for portions of said resist film in which latent images are formed, and

irradiating said resist film with electrons from said tip by supplying a second bias voltage between said tip and said substrate for portions of said resist film in which latent images are not formed,

wherein said first bias voltage is larger than said second bias voltage.

25. (New) The method of claim 24, wherein said tip contacts with said resist film during said exposing step and during said irradiating step.

26. (New) The method of claim 25, wherein said tip contacts with said resist film by a Coulomb force supplied from either of said first or second bias voltage between said tip and said substrate.

27. (New) The method of claim 24, wherein said second bias voltage is supplied so as not to form said latent images in said resist film.

28. (New) A fabrication apparatus, comprising,
an electrically conductive tip;
a first holder, which is used as a spring, for holding said tip;

a second holder for holding a substrate having a resist layer on a surface thereof;

a moving mechanism for said second holder; and

a device for supplying exposure current from said tip to said resist layer by supplying a voltage between said second holder and said tip, wherein

said first holder is deformed by a Coulomb force produced by said voltage, and

said substrate is relatively moved with said tip along an X-Y surface of said substrate while holding said tip in contact with said resist layer,

said device exposes said resist layer with electrons from said tip by supplying a first bias voltage between said tip and said substrate for portions of said resist layer in which latent images are formed, and irradiates said resist layer with electrons from said tip by supplying a second bias voltage between said tip and said substrate for portions of said resist layer in which latent images are not formed, and

where said first bias voltage is larger than said second bias voltage.